Wideband silicon germanium low-noise amplifier MMICRev. 2 — 11 April 2013Product data

Product data sheet

Product profile 1.

1.1 General description

The BGU7003W MMIC is a wideband amplifier in SiGe:C technology for high speed, low-noise applications in a plastic, leadless 6 pin, extremely thin small outline SOT886 package.

Application information Table 1.

 $T_{amb} = 25 \,^{\circ}C; V_{CC} = 2.85 \, V; I_{CC(tot)} = 3.2 \, mA \,^{[1]}; V_{ENABLE} \ge 0.7 \, V; f = 100 \, MHz; Z_S = Z_L = 50 \, \Omega \, unless$ otherwise specified. All measurements are done with the SMA-connectors as reference plane.

Application	NF	s ₂₁ ²	RL _{in}	RL _{out}	P _{i(1dB)}	P _{L(1dB)}	IP3 _I	IP3 ₀
	(dB)	(dB)	(dB)	(dB)	(dBm)	(dBm)	(dBm)	(dBm)
high-ohmic FM LNA	1.2	13	0.5	16.5	-23	-11	-15 <mark>2</mark>	-2 [2]

 $[1] \quad I_{CC(tot)} = I_{CC} + I_{RF_OUT} + I_{R_BIAS}.$

[2] The third order intercept point is measured at -30 dBm per tone at RF_IN (f₁ = 100 MHz; f₂ = 100.2 MHz)

1.2 Features and benefits

- Low noise high gain microwave MMIC
- Applicable between 40 MHz and 6 GHz
- Integrated temperature stabilized bias for easy design
- Bias current configurable with external resistor
- 110 GHz transit frequency SiGe:C technology
- Power-down mode current consumption < 1 μA</p>
- ESD protection > 1 kV Human Body Model (HBM) on all pins

1.3 Applications

- GPS
- FM LNA
- Low-noise amplifiers for microwave communications systems
- WLAN and CDMA applications
- Analog / digital cordless applications



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2. Pinning information

Table 2.	Pinning	
Pin	Description	Simplified outline Graphic symbol
1	R_BIAS	
2	RF_IN	$\square \square $
3	GND	
4	RF_OUT	
5	ENABLE	
6	V _{CC}	Transparent top view

3. Ordering information

Table 3. Ordering information						
Type number	Package	ge				
	Name	Description	Version			
BGU7003W	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886			

4. Marking

Table 4. Marking codes	
Type number	Marking code
BGU7003W	UW

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC}	supply voltage	RF input AC coupled		-	3.0	V
I _{CC(tot)}	total supply current	configurable with external resistor		-	25	mA
P _{tot}	total power dissipation	$T_{sp} \le 103 \ ^{\circ}C$	<u>[1]</u>	-	70	mW
T _{stg}	storage temperature			-65	+150	°C
Тj	junction temperature			-	150	°C

[1] T_{sp} is the temperature at the solder point of the ground lead.

6. Thermal characteristics

Table 6.	Thermal characteristics			
Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		235	K/W

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7. Characteristics

Table 7. Characteristics

 $T_{amb} = 25 \ ^{\circ}C; V_{CC} = 2.5 \ V; I_{CC(tot)} = 5.0 \ mA; V_{ENABLE} \ge 0.7 \ V \ unless \ otherwise \ specified. All measurements done on characterization board without matching, de-embedded up to the pins.$

			•			-	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CC}	supply voltage	RF input AC coupled		2.2	-	2.85	V
I _{CC(tot)}	total supply current	configurable with external resistor	<u>[1]</u>	3	-	15	mA
		$V_{\text{ENABLE}} \leq 0.4 \text{ V}$	[1]	-	-	0.001	mA
T _{amb}	ambient temperature			-40	+25	+85	°C
$ s_{21} ^2$	insertion power gain	T _{amb} = 25 °C					
		f = 100 MHz	[2]	21.0	22.5	-	dB
		f = 900 MHz	[2]	18.5	20.0	-	dB
		f = 1.575 GHz		16.0	17.5	-	dB
		f = 2.4 GHz	[2]	14.0	15.2	-	dB
		f = 5.8 GHz	[2]	10.0	11.4	-	dB
		$-40~^{\circ}C \leq T_{amb} \leq +85~^{\circ}C$					
		f = 100 MHz	[2]	20.0	22.5	-	dB
		f = 900 MHz	[2]	17.5	20.0	-	dB
		f = 1.575 GHz	[2]	15.0	17.5	-	dB
		f = 2.4 GHz	[2]	13.0	15.2	-	dB
		f = 5.8 GHz	[2]	9.0	11.4	-	dB
MSG	maximum stable gain	f = 100 MHz		-	33.8	-	dB
		f = 900 MHz		-	23.8	-	dB
		f = 1.575 GHz		-	20.5	-	dB
		f = 2.4 GHz		-	17.8	-	dB
		f = 5.8 GHz		-	15.4	-	dB
NF _{min}	minimum noise figure	f = 100 MHz		-	0.6	-	dB
		f = 900 MHz		-	0.6	-	dB
		f = 1.575 GHz		-	0.7	-	dB
		f = 2.4 GHz		-	0.8	-	dB
		f = 5.8 GHz		-	1.5	-	dB

[1] $I_{CC(tot)} = I_{CC} + I_{RF_{OUT}} + I_{R_{BIAS}}$.

[2] Guaranteed by design and characterization.

Table 8. ENABLE (pin 5)

 $-40 \ \mathcal{C} \le T_{amb} \le +85 \ \mathcal{C}$ State $\bigvee_{\mathsf{ENABLE}}(\mathsf{V})$ State ≤ 0.4 OFF ≥ 0.7 ON

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8. Application information

8.1 High-ohmic FM LNA

Table 9. Characteristics [1]

 $T_{amb} = 25 \text{ °C}$; $V_{CC} = 2.85 \text{ V}$; $I_{CC(tot)} = 3.2 \text{ mA} \frac{[2]}{2}$; $V_{ENABLE} \ge 0.7 \text{ V}$; f = 100 MHz; $Z_S = Z_L = 50 \Omega$ unless otherwise specified. All measurements are done with the SMA-connectors as reference plane.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
NF	noise figure		-	1.2	-	dB
$ s_{21} ^2$	Insertion power gain		-	13	-	dB
RL _{in}	input return loss		-	0.5	-	dB
RL _{out}	output return loss		-	16.5	-	dB
P _{i(1dB)}	input power at 1 dB gain compression		-	-23	-	dBm
P _{L(1dB)}	output power at 1 dB gain compression		-	-11	-	dBm
IP3 _I	input third-order intercept point	<u> </u>	[3]	-15	-	dBm
IP3 ₀	output third-order intercept point		[3]	-2	-	dBm

[1] See application note: AN11034 for details.

 $[2] \quad I_{CC(tot)} = I_{CC} + I_{RF_{OUT}} + I_{R_{BIAS}}.$

[3] The third order intercept point is measured at -30 dBm per tone at RF_IN (f₁ = 100 MHz; f₂ = 100.2 MHz)

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8.2 50 ohm FM LNA

Table 10. Characteristics^[1]

 $T_{amb} = 25 \ ^{\circ}C; V_{CC} = 2.8 \ V; I_{CC(tot)} = 4.3 \ mA \ ^{[2]}; V_{ENABLE} \ge 0.7 \ V; f = 100 \ MHz; Z_S = Z_L = 50 \ \Omega$ (input and output matched to 50 Ω) unless otherwise specified. All measurements are done with the SMA-connectors as reference plane.

	-					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
NF	noise figure		-	1.5	-	dB
$ s_{21} ^2$	Insertion power gain		-	15	-	dB
RL _{in}	input return loss		-	9	-	dB
RL _{out}	output return loss		-	14	-	dB
P _{i(1dB)}	input power at 1 dB gain compression		-	-20	-	dBm
P _{L(1dB)}	output power at 1 dB gain compression		-	-6	-	dBm
IP3 _I	input third-order intercept point	[3	1 -	-12.5	-	dBm
IP3 ₀	output third-order intercept point	[3	1 -	2.5	-	dBm
-						

[1] See application note AN11035 for details.

[2] $I_{CC(tot)} = I_{CC} + I_{RF_{OUT}} + I_{R_{BIAS}}$.

[3] The third order intercept point is measured at -30 dBm per tone at RF_IN (f₁ = 100 MHz; f₂ = 100.2 MHz)

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9. Package outline



Fig 10. Package outline SOT886 (XSON6)

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10. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

11. Soldering



12. Abbreviations

Table 11.	Abbreviations
Acronym	Description
AC	Alternating Current
CDMA	Code Division Multiple Access
DC	Direct Current
FM	Frequency Modulation
FR4	Flame Retardant 4
GPS	Global Positioning System
LNA	Low-Noise Amplifier
MMIC	Monolithic Microwave Integrated Circuit
RF	Radio Frequency
SiGe:C	Silicon Germanium Carbon
SMA	SubMiniature version A
WLAN	Wireless Local Area Network

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13. Revision history

Table 12. Revision histo	ory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BGU7003W v.2	20130411	Product data sheet	-	BGU7003W v.1
Modifications:	• Figure 10 on	page 9: figure has been updat	ed.	
BGU7003W v.1	20110830	Product data sheet	-	-

14. Legal information

14.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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